


Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. M122-2457	SERIAL NO. 10/735,355
 LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT: Zhongze Wang	
		FILING DATE December 12, 2003	GROUP 2811

U.S. PATENT DOCUMENTS							
Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
QM	AA	6,048,411	4/2000	Henley et al.			
QM	AB	6,071,783	6/2000	Liang et al.			
QM	AC	6,091,076	7/2000	Deleonibus			
QM	AD	6,245,729	2/2002	Maszara			
QM	AE	6,346,729	2/2002	Liang et al.			
QM	AF	6,358,791	3/2002	Hsu et al.			
QM	AG	6,403,485	6/2002	Quek et al.			
QM	AH	6,649,959	11/2003	Hsu et al.			
QM	AI	6,664,146	12/2003	Yu			
QM	AJ	<del>2005/0048844</del> 2002/004884	4/2002	Sakaguchi			
QM	AK	2002/0034844	3/2002	Yusukawa			
QM	AL	10/924,776		Ford			08/25/2004

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)			
QM	AM		Bashir et al., <i>Characterization of sidewall defects in selective epitaxial growth of silicon</i> , 13 J. VAC. SCI. TECHNOL. B, No. 3, pp. 923-927 (May/June 1995).
QM	AN		Bashir et al., <i>Reduction of sidewall defect induced leakage currents by the use of nitrided field oxides in silicon selective epitaxial growth</i> ..., 18 J. Vac. Sci. Technol. B, No. 2, pp. 695-699 (March/April 2000).
QM	AO		Hammad et al., <i>The Pseudo-Two-Dimensional Approach to Model the Drain Section in SOI MOSFETs</i> , 48 IEEE TRANSACTIONS ON ELECTRON DEVICES, No. 2, pp. 386-387 (February 2001).
QM	AP		Sivagnaname et al., <i>Stand-by Current in PD-SOI Pseudo-nMOS Circuits</i> , IEEE, pp. 95-96 (2003)
QM	AO		Wang et al., <i>Achieving Low Junction Capacitance on Bulk SI MOSFET Using SDOI Process</i> , Micron Technology, Inc., 12 pages (pre-2004).
EXAMINER		DATE CONSIDERED	
J. M. Kennedy		August 26, 2005	
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.			

Form PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MI22-2457	SERIAL NO. 10735,355
LIST OF ART CITED BY APPLICANT (Use several sheets if necessary)		APPLICANT: Zhongze Wang	
		FILING DATE December 12, 2003	GROUP 2811

U.S. PATENT DOCUMENTS							
Examiner's Initials		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
QM	AA	6,048,411	4/2000	Henley et al.			
QM	AB	6,071,783	6/2000	Liang et al.			
QM	AC	6,091,076	7/2000	Deleonibus			
QM	AD	6,245,729	2/2002	Maszara			
QM	AE	6,346,729	2/2002	Liang et al.			
QM	AF	8,358,791	3/2002	Hsu et al.			
QM	AG	6,403,485	6/2002	Quek et al.			
QM	AH	6,649,959	11/2003	Hsu et al.			
QM	AI	6,664,146	12/2003	Yu			
QM	AJ	<del>2002/004884</del> 2002/004884	4/2002	Sakaguchi			
QM	AK	2002/0034844	3/2002	Yusukawa			
QM	AL	10/924,776		Ford			08/25/2004

OTHER REFERENCES (including Author, Title, Date, Pertinent Pages, Etc.)		
Q	AM	Bashir et al., <i>Characterization of sidewall defects in selective epitaxial growth of silicon</i> , 13 J. Vac. Sci. Technol. B, No. 3, pp. 923-927 (May/June 1995).
QM	AN	Bashir et al., <i>Reduction of sidewall defect induced leakage currents by the use of nitrided field oxides in silicon selective epitaxial growth</i> ..., 18 J. Vac. Sci. Technol. B, No. 2, pp. 695-699 (March/April 2000).
QM	AO	Hammad et al., <i>The Pseudo-Two-Dimensional Approach to Model the Drain Section in SOI MOSFETs</i> , 48 IEEE TRANSACTIONS ON ELECTRON DEVICES, No. 2, pp. 386-387 (February 2001).
QM	AP	Sivagnaname et al., <i>Stand-by Current in PD-SOI Pseudo-nMOS Circuits</i> , IEEE, pp. 95-96 (2003)
QM	AQ	Wang et al., <i>Achieving Low Junction Capacitance on Bulk SI MOSFET Using SDOI Process</i> , Micron Technology, Inc., 12 pages (pre-2004).
EXAMINER		DATE CONSIDERED
Kenneth M. Kennedy		August 22, 2005

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.